



Fig. 1. SnO film thickness as function of number of ALD cycles. The ALD conditions were a Sn(EtCp)<sub>2</sub> pulse time of 10.0 s, a H<sub>2</sub>O pulse time of 3.0 s, and a growth temperature of 200 °C. H<sub>2</sub> plasma pulse times were 5 s (●) and 1 s (◆), respectively.